## Switch-mode Power Rectifiers

**DPAK Surface Mount Package** 

# MBRD320G, MBRD330G, MBRD340G, MBRD350G, MBRD360G

These state-of-the-art devices are designed for use as output rectifiers, free wheeling, protection and steering diodes in switching power supplies, inverters and other inductive switching circuits.

#### **Features**

- Extremely Fast Switching
- Extremely Low Forward Drop
- Platinum Barrier with Avalanche Guardrings
- NRVBD and SBRD Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### **Mechanical Characteristics:**

- Case: Epoxy, Molded
- Weight: 0.4 Gram (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes; 260°C Max. for 10 Seconds
- ESD Ratings:
  - ◆ Machine Model = C
  - ♦ Human Body Model = 3B



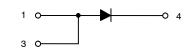
ON Semiconductor®

www.onsemi.com

# SCHOTTKY BARRIER RECTIFIERS 3.0 AMPERES, 20 – 60 VOLTS



DPAK CASE 369C



## **MARKING DIAGRAM**



A = Assembly Location\*

Y = Year

WW = Work Week
B3x0 = Device Code
x = 2, 3, 4, 5, or 6
G = Pb-Free Package

\* The Assembly Location Code (A) is front side optional. In cases where the Assembly Location is stamped in the package bottom (molding ejecter pin), the front side assembly code may be blank.

## **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

#### **MAXIMUM RATINGS**

Datie.	Symbol	MBRD/SBRD8			1114		
Rating		320	330	340	350	360	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		20	30	40	50	60	V
Average Rectified Forward Current (T <sub>C</sub> = +125°C)	I <sub>F(AV)</sub>		3		Α		
Peak Repetitive Forward Current, T <sub>C</sub> = +125°C (Square Wave, Duty = 0.5)	I <sub>FRM</sub>	6		Α			
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I <sub>FSM</sub>	75		Α			
Peak Repetitive Reverse Surge Current (2 μs, 1 kHz)	I <sub>RRM</sub>	1		Α			
Operating Junction Temperature Range (Note 1)	T <sub>J</sub>	−65 to +175		°C			
Storage Temperature Range	T <sub>stg</sub>	-65 to +175		°C			
Voltage Rate of Change (Rated V <sub>R</sub> )	dv/dt	10,000		V/μs			

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance, Junction-to-Case	$R_{ heta JC}$	6	°C/W
Maximum Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	80	°C/W

<sup>2.</sup> Rating applies when surface mounted on the minimum pad size recommended.

## **ELECTRICAL CHARACTERISTICS**

Characteristic	Symbol	Value	Unit
$\label{eq:maximum Instantaneous Forward Voltage (Note 3)} \begin{subarray}{l} \textbf{i}_F = 3 \text{ Amps, } \textbf{T}_C = +25^{\circ}\textbf{C} \\ \textbf{i}_F = 3 \text{ Amps, } \textbf{T}_C = +125^{\circ}\textbf{C} \\ \textbf{i}_F = 6 \text{ Amps, } \textbf{T}_C = +25^{\circ}\textbf{C} \\ \textbf{i}_F = 6 \text{ Amps, } \textbf{T}_C = +125^{\circ}\textbf{C} \\ \end{subarray}$	V <sub>F</sub>	0.6 0.45 0.7 0.625	V
Maximum Instantaneous Reverse Current (Note 3) (Rated dc Voltage, T <sub>C</sub> = +25°C) (Rated dc Voltage, T <sub>C</sub> = +125°C)	İR	0.2 20	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

<sup>1.</sup> The heat generated must be less than the thermal conductivity from Junction-to-Ambient:  $dP_D/dT_J < 1/R_{\theta JA}$ .

<sup>3.</sup> Pulse Test: Pulse Width = 300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MBRD320G		75 Units / Rail
SBRD8320G*		75 Units / Rail
SBRD8320G-VF01*		75 Units / Rail
MBRD320RLG		1,800 Tape & Reel
MBRD320T4G		2,500 Tape & Reel
SBRD8320T4G*		2,500 Tape & Reel
SBRD8320T4G-VF01*		2,500 Tape & Reel
MBRD330G		75 Units / Rail
SBRD8330G*		75 Units / Rail
SBRD8330G-VF01*		75 Units / Rail
MBRD330RLG		1,800 Tape & Reel
MBRD330T4G		2,500 Tape & Reel
SBRD8330T4G*		2,500 Tape & Reel
SBRD8330T4G-VF01*		2,500 Tape & Reel
MBRD340G		75 Units / Rail
SBRD8340G*		75 Units / Rail
SBRD8340G-VF01*		75 Units / Rail
MBRD340RLG		1,800 Tape & Reel
MBRD340T4G		2,500 Tape & Reel
SBRD8340T4G*	DPAK (Pb-Free)	2,500 Tape & Reel
SBRD8340T4G-VF01*	( 2	2,500 Tape & Reel
MBRD350G		75 Units / Rail
SBRD8350G*		75 Units / Rail
SBRD8350G-VF01*		75 Units / Rail
MBRD350RLG		1,800 Tape & Reel
SBRD8350RLG*		1,800 Tape & Reel
SBRD8350RLG-VF01*		1,800 Tape & Reel
MBRD350T4G		2,500 Tape & Reel
SBRD8350T4G*		2,500 Tape & Reel
SBRD8350T4G-VF01*		2,500 Tape & Reel
MBRD360G		75 Units / Rail
SBRD8360G*		75 Units / Rail
SBRD8360G-VF01*		75 Units / Rail
MBRD360RLG		1,800 Tape & Reel
SBRD8360RLG*		1,800 Tape & Reel
SBRD8360RLG-VF01*	]	1,800 Tape & Reel
MBRD360T4G		2,500 Tape & Reel
NRVBD360VT4G*		2,500 Tape & Reel
SBRD8360T4G*	1	2,500 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>NRVBD and SBRD Prefixes for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

## **TYPICAL CHARACTERISTICS**

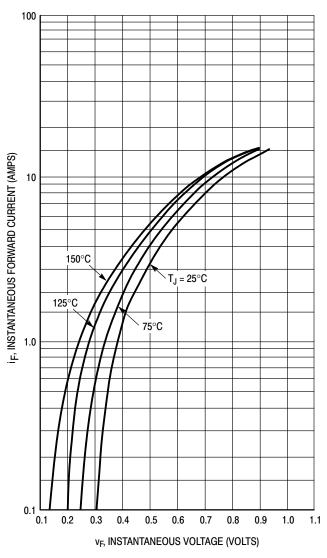
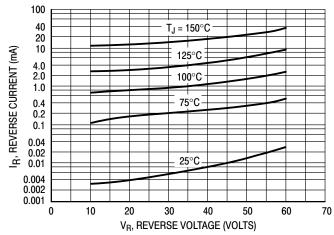


Figure 1. Typical Forward Voltage



\*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these curves if  $V_R$  is sufficient below rated  $V_R$ .

**Figure 2. Typical Reverse Current** 

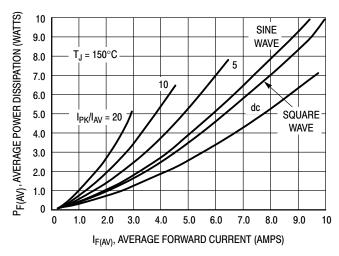


Figure 3. Average Power Dissipation

## **TYPICAL CHARACTERISTICS**

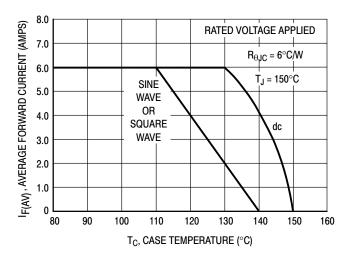


Figure 4. Current Derating, Case

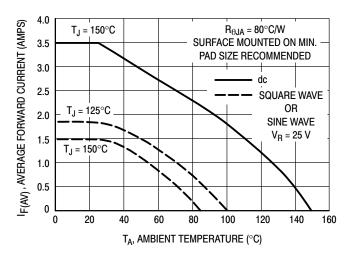


Figure 5. Current Derating, Ambient

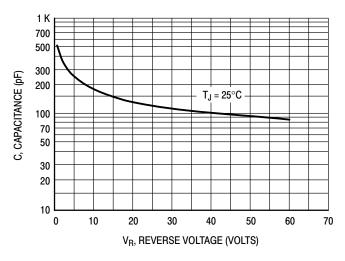
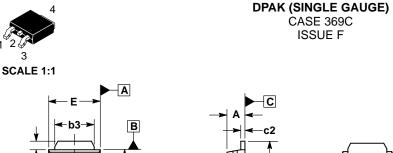
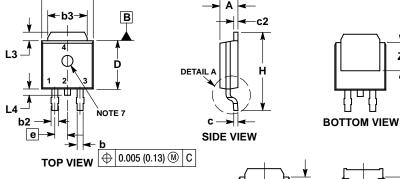
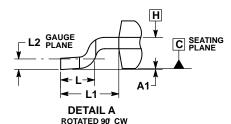


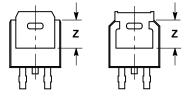
Figure 6. Typical Capacitance

**DATE 21 JUL 2015** 





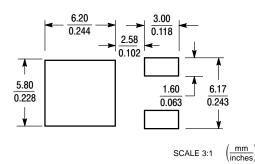




**BOTTOM VIEW** ALTERNATE CONSTRUCTIONS

STYLE 1: PIN 1. BASE 2. COLLE 3. EMITTI 4. COLLE	ER 3. SOL	AIN 2. CATI JRCE 3. ANO	HODE 2. ANODE DE 3. GATE	STYLE 5: PIN 1. GATE 2. ANODE 3. CATHODE 4. ANODE
STYLE 6:	STYLE 7:	3. ANODE	STYLE 9:	STYLE 10:
PIN 1. MT1	PIN 1. GATE		PIN 1. ANODE	PIN 1. CATHODE
2. MT2	2. COLLECTOR		2. CATHODE	2. ANODE
3. GATE	3. EMITTER		3. RESISTOR ADJUST	3. CATHODE
4. MT2	4. COLLECTOR		4. CATHODE	4. ANODE

## **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## NOTES:

z

- IOTES. 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: INCHES. 3. THERMAL PAD CONTOUR OPTIONAL WITHIN DI-

- MENSIONS b3, L3 and Z.

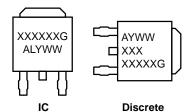
  Jimensions b And E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.

  MENSIONS D AND E ARE DETERMINED AT THE
- OUTERMOST EXTREMES OF THE PLASTIC BODY.

  6. DATUMS A AND B ARE DETERMINED AT DATUM
- 7. OPTIONAL MOLD FEATURE.

		INC	HES	MILLIM	IETERS
	DIM	MIN	MAX	MIN	MAX
	Α	0.086	0.094	2.18	2.38
	A1	0.000	0.005	0.00	0.13
	b	0.025	0.035	0.63	0.89
ĺ	b2	0.028	0.045	0.72	1.14
	b3	0.180	0.215	4.57	5.46
	С	0.018	0.024	0.46	0.61
	c2	0.018	0.024	0.46	0.61
	D	0.235	0.245	5.97	6.22
	Е	0.250	0.265	6.35	6.73
	е	0.090	BSC	2.29	BSC
	Н	0.370	0.410	9.40	10.41
	L	0.055	0.070	1.40	1.78
	L1	0.114	REF	2.90	REF
ĺ	L2	0.020	BSC	0.51	BSC
	L3	0.035	0.050	0.89	1.27
	L4		0.040		1.01
	Z	0.155		3.93	

## **GENERIC MARKING DIAGRAM\***



XXXXXX = Device Code = Assembly Location Α L = Wafer Lot Υ = Year

WW = Work Week G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking.

DOCUMENT NUMBER:	98AON10527D	E
STATUS:	ON SEMICONDUCTOR STANDARD	a ve
NEW STANDARD:	REF TO JEDEC TO-252	"(
DESCRIPTION:	DPAK SINGLE GAUGE SURFACE MOU	NT

Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.

PAGE 1 OF 2



<b>DOCUMENT</b>	NUMBER:
98AON10527	7D

PAGE 2 OF 2

ISSUE	REVISION	DATE
0	RELEASED FOR PRODUCTION. REQ. BY L. GAN	24 SEP 2001
Α	ADDED STYLE 8. REQ. BY S. ALLEN.	06 AUG 2008
В	ADDED STYLE 9. REQ. BY D. WARNER.	16 JAN 2009
С	ADDED STYLE 10. REQ. BY S. ALLEN.	09 JUN 2009
D	RELABELED DRAWING TO JEDEC STANDARDS. ADDED SIDE VIEW DETAIL A. CORRECTED MARKING INFORMATION. REQ. BY D. TRUHITTE.	29 JUN 2010
E	ADDED ALTERNATE CONSTRUCTION BOTTOM VIEW. MODIFIED DIMENSIONS b2 AND L1. CORRECTED MARKING DIAGRAM FOR DISCRETE. REQ. BY I. CAMBALIZA.	06 FEB 2014
F	ADDED SECOND ALTERNATE CONSTRUCTION BOTTOM VIEW. REQ. BY K. MUSTAFA.	21 JUL 2015

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ON Semiconductor and the are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and

#### **PUBLICATION ORDERING INFORMATION**

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

ON Semiconductor Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative